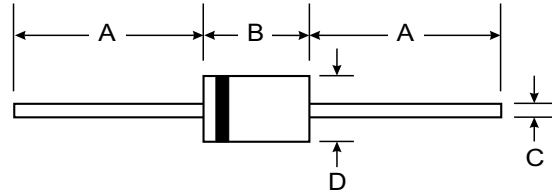
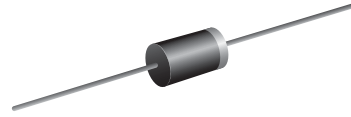


**VOLTAGE RANGE: 90 - 100V**  
**CURRENT: 3.3 A**

### Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability



DO-201AD		
Dim	Min	Max
A	25.40	—
B	7.20	9.50
C	1.20	1.30
D	4.80	5.30
All Dimensions in mm		

### Mechanical Data

- Case: DO-201AD, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 1.2 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



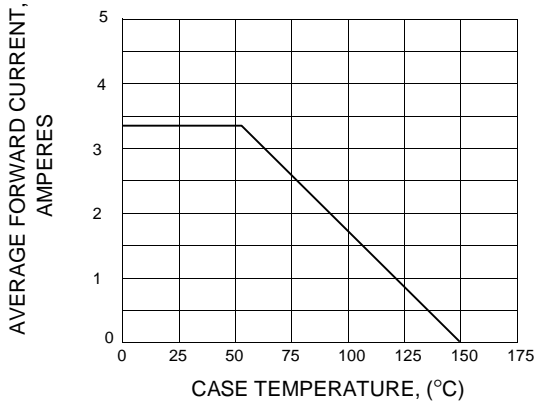
### Maximum Ratings and Electrical Characteristics T<sub>A</sub> = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

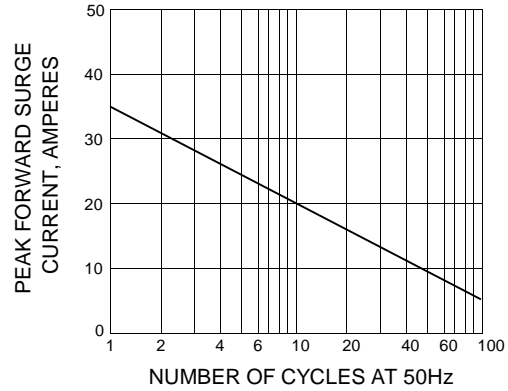
Characteristic	Symbol	31DQ09	31DQ10	Unit
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	90	100	V
Maximum DC Blocking Voltage	V <sub>DC</sub>	90	100	V
Maximum Average Forward Current at Ambient Temperature, T <sub>c</sub> = 53 °C	I <sub>F(AV)</sub>	3.3		A
Maximum Non-repetitive Peak Forward Surge Current ( 50 Hz, Sine wave, 10ms )	I <sub>FSM</sub>	34		A
Maximum Forward Voltage at I <sub>F</sub> = 3.0 A	V <sub>F</sub>	0.85		V
Maximum Reverse Current at V <sub>R</sub> = V <sub>RRM</sub> , T <sub>j</sub> = 25°C	I <sub>R</sub>	1.0		mA
Maximum Reverse Current at V <sub>R</sub> = V <sub>RRM</sub> , T <sub>j</sub> = 125°C	I <sub>RM</sub>	3.0		mA
Junction Temperature Range	T <sub>J</sub>	- 40 to + 150		°C
Storage Temperature Range	T <sub>STG</sub>	- 40 to + 150		°C

**RATING AND CHARACTERISTIC CURVES ( 31DQ09 - 31DQ10 )**

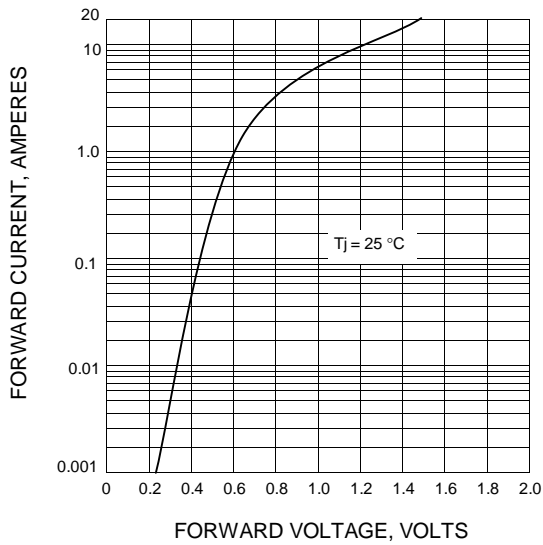
**FIG.1 - FORWARD CURRENT DERATING CURVE**



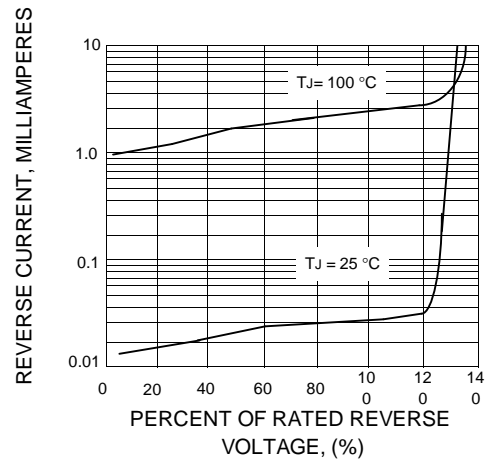
**FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT**



**FIG.3 - TYPICAL FORWARD CHARACTERISTICS**



**FIG.4 - TYPICAL REVERSE CHARACTERISTICS**



单击下面可查看定价，库存，交付和生命周期等信息

[>>SUNMATE\(森美特\)](#)